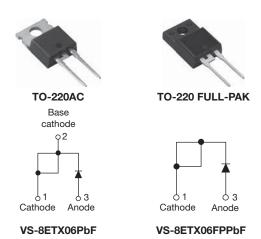


Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt®

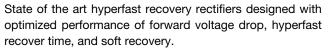


PRODUCT SUMMARY					
Package	TO-220AC, TO-220FP				
I _{F(AV)}	8 A				
V_{R}	600 V				
V _F at I _F	3.0 V				
t _{rr} (typ.)	15 ns				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- · Hyperfast recovery time
- Benchmark ultralow forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V_{RRM}		600	V			
Average restified forward current	1	T _C = 143 °C	8				
Average rectified forward current FULL-PAK	$T_{C} = 106 ^{\circ}C$	0	Α				
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	110	A			
Repetitive peak forward current	I _{FM}		18				
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	ı	-	,,	
Forward voltage V	V _E	I _F = 8 A	-	2.3	3.0	V	
	٧F	I _F = 8 A, T _J = 150 °C	-	1.4	1.7		
Poverse leakage current	I_	$V_R = V_R$ rated	-	0.3	50		
Reverse leakage current I _R		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	35	500	μΑ	
Junction capacitance	C _T	V _R = 600 V	-	17	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

Document Number: 94032 Revision: 28-Apr-11

VS-8ETX06PbF, VS-8ETX06FPPbF

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	15	19		
Reverse recovery time	+	I _F = 8 A, dI _F /dt = 100	A/ μ s, V _R = 30 V	-	16	24	ne	
neverse recovery time	t _{rr}	T _J = 25 °C		-	17	-	ns	
		T _J = 125 °C -	-	40	-			
Peak recovery current	I _{RRM}	T _J = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	2.3	-	А	
Feak recovery current		T _J = 125 °C		-	4.5	-		
Reverse recovery charge		T _J = 25 °C		-	20	-	nC	
heverse recovery charge	Q _{rr}	T _J = 125 °C		-	100	-	110	
Reverse recovery time	t _{rr}		I _F = 8 A dI _F /dt = 600 A/μs	-	31	-	ns	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	12	-	Α	
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	195	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDTIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range			- 65	-	175	°C	
Thermal resistance,	D		ı	1.4	2		
junction to case (FULL-PAK)	R _{thJC}		-	3.4	4.3		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Maight			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking daying		Case style TO-220AC	8ETX06		X06		
Marking device		Case style TO-220 FULL-PAK		8ETX	06FP		

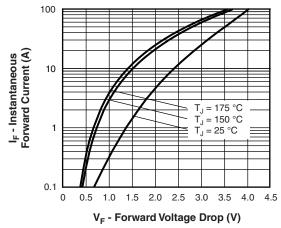


Fig. 1 - Typical Forward Voltage Drop Characteristics

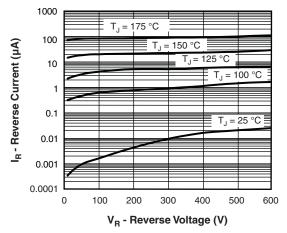


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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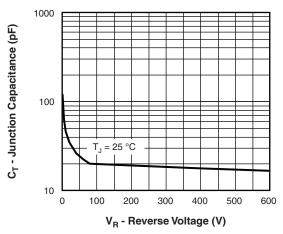


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

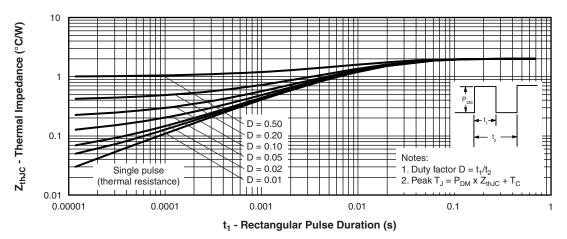


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

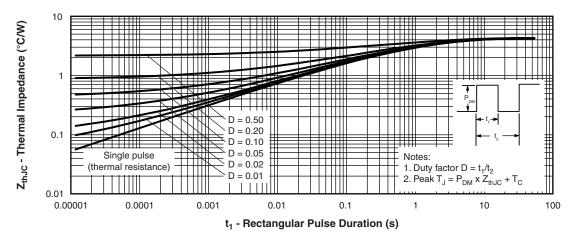


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

VS-8ETX06PbF, VS-8ETX06FPPbF

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



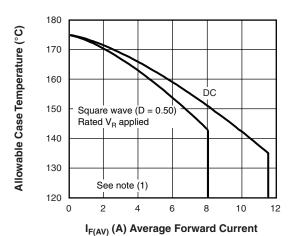


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

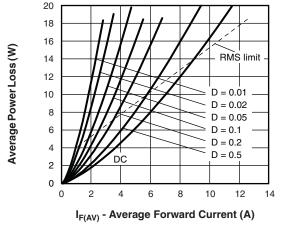


Fig. 8 - Forward Power Loss Characteristics

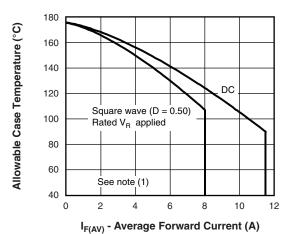


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

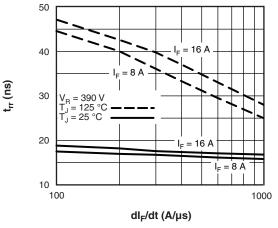


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

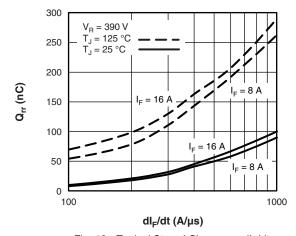


Fig. 10 - Typical Stored Charge vs. dI_F/dt

Note

(1) Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 8); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R



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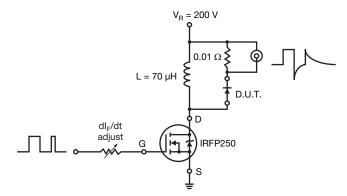
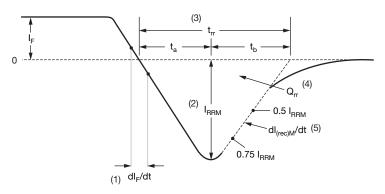


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going $I_{\rm F}$ to point where a line passing through 0.75 $I_{\rm RRM}$ and 0.50 $I_{\rm RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

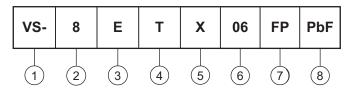
VS-8ETX06PbF, VS-8ETX06FPPbF

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Current rating (8 = 8 A)

E = Single diode

T = TO-220, DPAK

X = Hyperfast rectifier

Voltage rating (06 = 600 V)

• None = TO-220AC

• FP = TO-220 FULL-PAK

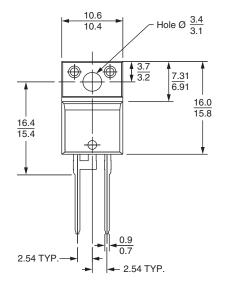
8 PbF = Lead (Pb)-free

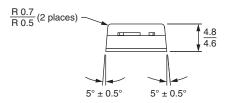
Tube standard pack quantity: 50 pieces

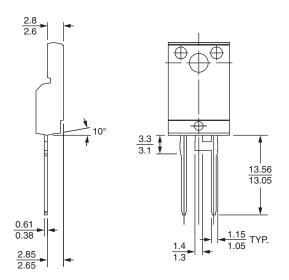
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-220AC	www.vishay.com/doc?95221			
Dimensions	TO-220AC FULL-PAK	www.vishay.com/doc?95005			
Part marking information	TO-220AC	www.vishay.com/doc?95224			
	TO-220AC FULL-PAK	www.vishay.com/doc?95009			
SPICE model		www.vishay.com/doc?95393			

Vishay Semiconductors

DIMENSIONS in millimeters







Lead assignments

<u>Diodes</u> 1 + 2 - Cathode 3 - Anode

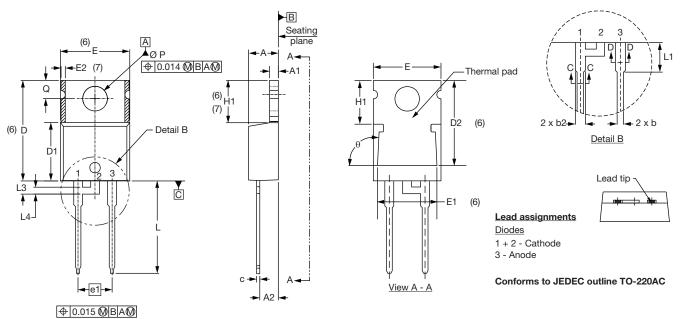
Conforms to JEDEC outline TO-220 FULL-PAK



Vishay Semiconductors

TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIMETERS		INCHES		INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		
E1	6.86	8.89	0.270	0.350	6		
E2	-	0.76	-	0.030	7		
е	2.41	2.67	0.095	0.105			
e1	4.88	5.28	0.192	0.208			
H1	6.09	6.48	0.240	0.255	6, 7		
L	13.52	14.02	0.532	0.552			
L1	3.32	3.82	0.131	0.150	2		
L3	1.78	2.13	0.070	0.084			
L4	0.76	1.27	0.030	0.050	2		
ØΡ	3.54	3.73	0.139	0.147			
Q	2.60	3.00	0.102	0.118			
θ	90° t	o 93°	90° to 93°				

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline





Vishay

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